

## **ABSTRACT**

Disclosed is a method of manufacturing a semiconductor wafer. In the present invention, a nucleation site is formed in a region deep into the wafer through  
5 low-temperature annealing process, and oxygen or precipitation material, the metallic impurity, or the like is trapped in the nucleation site through rapid thermal annealing process. As a gettering effect is improved using the rapid thermal annealing process, the concentration of the impurity on the surface of the wafer can be lowered and the reliability of the device could be improved,. Further, the  
10 annealing steps can be reduced than the prior art and the productivity of the device can thus be increased.